

**substance: boron compounds, general properties**  
**property: further structure groups**

**Structure group of YB<sub>25</sub>**

Structure: monoclinic [97T, 99M]

Space group: I112, I11m, or I112/m

Isostructural compounds with lanthanoides from Gd to Ho are possible as well.

Because of the very similar lattice parameters of YB<sub>25</sub> and YAlB<sub>14</sub> it is assumed that the structure is very similar to that of the orthorhombic MgAlB<sub>14</sub> type borides [97T, 99M].

Information on the electronic properties is still missing

**Structure group of BeB<sub>3</sub>**

87L,  
75M

Information on the electronic properties is still missing.

**Structure group of orthorhombic SiB<sub>6</sub>**

87L,  
86V

Information on the electronic properties is missing.

**Structure group of the YB<sub>66</sub> type borides**

Many of the lanthanide metals form boron-rich compounds of the composition MB<sub>66</sub>. The compounds NdB<sub>66</sub>, SmB<sub>66</sub>, GdB<sub>66</sub>, TbB<sub>66</sub>, DyB<sub>66</sub>, HoB<sub>66</sub>, ErB<sub>66</sub>, TmB<sub>66</sub>, YbB<sub>66</sub>, LuB<sub>66</sub> are known at now. [72S1, 72S2, 72S3, 76K, 76S, 77N, 77S2, 75B, 81S].

The boron framework is composed of (B<sub>12</sub>)<sub>13</sub> giant icosahedra consisting of a central and 12 surrounding B<sub>12</sub> icosahedra and B<sub>80</sub> clusters. The (B<sub>12</sub>)<sub>13</sub> units are located in one orientation at the face-centered cubic lattice points. They also occur at the centers of the cell and of the cell edges with orientation rotated by 90°. In total they contribute with eight (B<sub>12</sub>)<sub>13</sub> units = 1248 boron atoms to the unit cell (Fig. 1). The B<sub>80</sub> clusters consist of 80 boron sites belonging to four crystallographic positions of the space group Fm3c: (3×192j, 64g)/8. In this cluster, all the sites are only partially occupied with occupancies ranging between 28 and 71 % leading to about 42 boron atoms per B<sub>80</sub> cluster in agreement with previous structure description [69R]. The B<sub>80</sub> cluster is centered at the 8(a) position (1/4, 1/4, 1/4), and thus there are eight of such clusters (336 B atoms) per unit cell. Accordingly, the total number of B atoms is 1584 per unit cell. The Y sites are enclosing the B<sub>80</sub> clusters in an octahedral arrangement, each, hence there are eight octahedral Y arrangements per unit cell. They are connected to their neighboring six octahedra through their apical Y sites (Fig. 1). The actual composition is determined by the occupancy of the Y sites, for example 0.5, 0.5324 and 0.575(5) for YB<sub>66</sub>, YB<sub>62</sub> and YB<sub>56</sub> respectively. In the case of simultaneously occupied neighbored Y sites (for occupancies > 0.5 inevitable) the repulsive force between the ionized Y atoms increases the Y-Y distance [97H].

### Representatives of the YB<sub>66</sub> type borides

Chemical formula (idealized)	Structural formula	
YB <sub>66</sub>	Y <sub>3</sub> ·(B <sub>12</sub> ) <sub>13</sub> ·B <sub>42</sub>	97H
YB <sub>62</sub>	Y <sub>3.2</sub> ·(B <sub>12</sub> ) <sub>13</sub> ·B <sub>42</sub>	77I
YB <sub>56</sub>	Y <sub>3.5</sub> ·(B <sub>12</sub> ) <sub>13</sub> ·B <sub>42</sub>	97H
GdB <sub>66</sub>		94G
DyB <sub>66</sub>		86G

So far as electronic properties of representatives of the YB<sub>66</sub> type borides have become known, they indicate semiconducting behavior.

### Thermal properties

Temperature dependence of the thermal conductivity of some representatives of the YB<sub>66</sub> structure group: YB<sub>66±x</sub> (YB<sub>61.7</sub> [92R, 94M]; YB<sub>66</sub> [71S, 94M], YB<sub>66</sub> [87C, 89C, 94M; YB<sub>66</sub> [77S2, 94M]); GdB<sub>66±x</sub> (GdB<sub>66</sub> [86G]; GdB<sub>62.5</sub> [94M]) in Fig. 2.

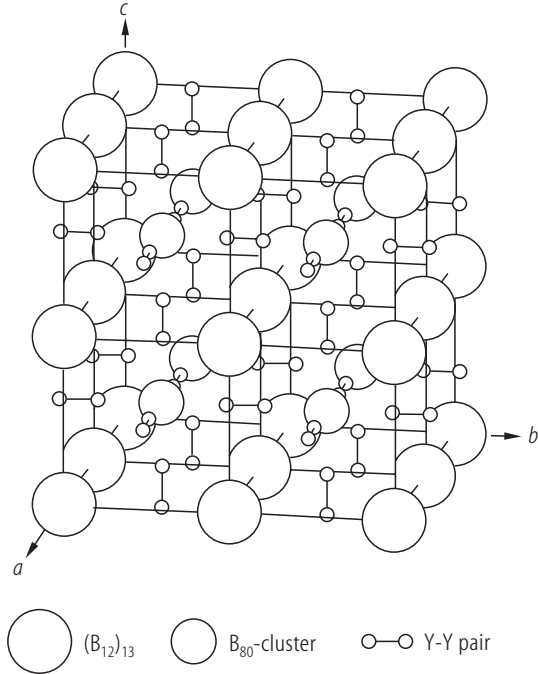
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**Fig. 1.**

YB<sub>66</sub> structure group. Structure containing (B<sub>12</sub>)<sub>13</sub> giant icosahedra, B<sub>80</sub> clusters (80 B sites, about 42 of which are statistically occupied) and Y-Y pairs [97H].

YB<sub>66</sub> structure group



**Fig. 2.**

YB<sub>66</sub> structure group. Temperature dependence of thermal conductivity. Open symbols: YB<sub>66±X</sub> (squares, YB<sub>61.7</sub> [92R, 94M]; triangles, YB<sub>66</sub> [71S, 94M], circles, YB<sub>66</sub> [87C, 89C, 94M], diamonds, YB<sub>66</sub> [77S1, 94M]); closed symbols: GdB<sub>66±X</sub> (circles, GdB<sub>66</sub> [86G], triangles down, GdB<sub>62.5</sub> [94M]).

